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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/072,145	02/07/2002	Guy E. Averett	ONS00317	1448
7:	590 06/29/2005		EXAM	INER
ON Semiconductor			MAGEE, THOMAS J	
Patent Administration Dept - MD A700 P.O. Box 62890			ART UNIT	PAPER NUMBER
Phoenix, AZ 85082-2890			2811	
	•		DATE MAILED: 06/29/2005	

Please find below and/or attached an Office communication concerning this application or proceeding.

		Si Si			
	Application No.	Applicant(s)			
Office Action Summary	10/072,145	AVERETT ET AL.			
Office Action Summary	Examiner	Art Unit			
7. 444.000	Thomas J. Magee	2811			
The MAILING DATE of this communication app Period for Reply	ears on the cover sheet with the c	orrespondence address			
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION.  - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication.  - If the period for reply specified above is less than thirty (30) days, a reply If NO period for reply is specified above, the maximum statutory period w  - Failure to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may a reply be tin within the statutory minimum of thirty (30) day will apply and will expire SIX (6) MONTHS from cause the application to become ABANDONE	nely filed s will be considered timely. the mailing date of this communication. D (35 U.S.C. § 133).			
Status					
1) ☐ Responsive to communication(s) filed on 12 April 2005.  2a) ☐ This action is FINAL. 2b) ☐ This action is non-final.  3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under Ex parte Quayle, 1935 C.D. 11, 453 O.G. 213.					
Disposition of Claims					
<ul> <li>4)  Claim(s) 1-11 and 26-33 is/are pending in the application.</li> <li>4a) Of the above claim(s) is/are withdrawn from consideration.</li> <li>5)  Claim(s) 1-9, and 26-32 is/are allowed.</li> <li>6)  Claim(s) 10,11 and 33 is/are rejected.</li> <li>7)  Claim(s) is/are objected to.</li> <li>8)  Claim(s) are subject to restriction and/or election requirement.</li> </ul>					
Application Papers					
9) The specification is objected to by the Examiner.  10) The drawing(s) filed on is/are: a) accepted or b) objected to by the Examiner.  Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).					
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).  11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.					
Priority under 35 U.S.C. § 119					
12) Acknowledgment is made of a claim for foreign  a) All b) Some * c) None of:  1. Certified copies of the priority documents  2. Certified copies of the priority documents  3. Copies of the certified copies of the priority application from the International Bureau  * See the attached detailed Office action for a list	s have been received. s have been received in Applicati rity documents have been receive u (PCT Rule 17.2(a)).	on No ed in this National Stage			
Attachment(s)					
1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date	4) Interview Summary Paper No(s)/Mail D: 5) Notice of Informal F 6) Other:				

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#### **DETAILED ACTION**

## Claim Objections

1. Claim 26 is objected to on the basis of a minor informality. The phrase, "a thermal oxide layer grown on the semiconductor layer to form a seal the opening," appears to have a typographical error. Examiner assumes that Applicant meant to recite, "a thermal oxide layer grown on the semiconductor layer to seal the opening." Correction is required.

### Claim Rejections – 35 U.S.C. 112

- 2. The following is a quotation of the second paragraph of 35 U.S.C. 112:
- The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.
- 3. Claims 10, 11, and 33 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention. The terms, "amorphous" and "poly[silicon]" are microstructural descriptions and not not compositional descriptors. Further, although polysilicon and amorphous silicon may be high resistivity materials, neither are classed as dielectrics. Hence, the limitations, "the third dielectric layer comprises polysilicon," and "the third dielectric layer comprises amorphous silicon," are unclear. Correction and/or clarification is required.
- 4. Claims 7 and 32 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention. Within both claims there is no limitation describing or

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identifying the second dielectric layer and the relationship to a first and third dielectric layer. Correction and/or clarification is required.

#### Allowable Subject Matter

4. Claims 1 – 9, and 26 – 32 are allowed. The prior art of record do not reasonably teach or suggest, either singularly or in combination, the limitation in Claim 1 of a semiconductor device comprising "a semiconductor substrate having a surface formed with a first recessed region: a first dielectric material deposited in the first recessed region and formed with a second recessed region having walls; a semi-conductor layer formed in proximity to the second recessed region; and a thermal oxide layer formed integral with the semiconductor layer, wherein the thermal oxide layer seals the second recessed region while leaving a void in the second recessed region."

In like fashion, the prior art of record do not reasonably teach or suggest, either singularly or in combination, the limitation in Claim 26 of a semiconductor device comprising, "a semiconductor substrate having a surface formed with a first recessed region; a first dielectric material deposited in the first recessed region and formed with a second recessed region having an opening and walls; a semiconductor cap layer formed adjacent the opening; and a thermal oxide layer grown on the semiconductor layer to seal the opening."

#### Conclusions

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5. Any inquiry concerning this communication or earlier communications from the

Examiner should be directed to Thomas Magee, whose telephone number is (571) 272

1658. The Examiner can normally be reached on Monday through Friday from 8:30AM

to 5:00PM (EST). If attempts to reach the Examiner by telephone are unsuccessful, the

examiner's supervisor, Eddie Lee, can be reached on (571) 272-1732. The fax

number for the organization where this application or proceeding is assigned is (703)

872-9306.

Thomas Magee June 2, 2005

Stoven Loke
Primary Examiner